

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Taketomi Asami et al. Art Unit : Unknown
Serial No. : New Divisional Application Examiner : Unknown
Filed : March 4, 2004
Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

Commissioner for Patents
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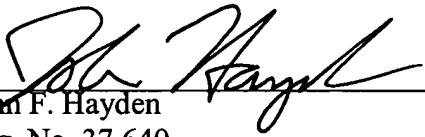
INFORMATION DISCLOSURE STATEMENT

Under 35 USC §120, this application relies on the earlier filing date of application serial number 09/918,547, filed on August 1, 2001. The attached list of references were submitted to and/or cited by the Office in the prior application and, therefore, are not provided in this application.

This statement is being filed with the application. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: March 4, 2004


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Substitute Form PTO-1449 (Modified)		U.S. Department of Commerce Patent and Trademark Office		Attorney's Docket No. 12732-061002		Application No. New Divisional Application	
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Taketomi Asami et al.					
		Filing Date March 4, 2004		Group Art Unit			
U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	2001/0014535 A1	08/16/2001	Yamazaki			
	AB	2002/0014625 A1	02/07/2002	Asami et al.			
	AC	2002/0038889 A1	04/04/2002	Yamazaki et al.			
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Examiner Signature				Date Considered			
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	ABB	6,690,068	02/10/2004	Yamazaki et al.			

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							Yes	No
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Examiner Signature	Date Considered
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